

Michel Pons

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

163
papers

1,935
citations

22
h-index

34
g-index

191
ext. papers

2,069
ext. citations

2.3
avg, IF

4.22
L-index

#	Paper	IF	Citations
163	Modeling multilayer coating systems in solar receivers. <i>Surface and Coatings Technology</i> , 2020 , 399, 1261-1272	4.4	0
162	Chemical vapor deposition of titanium nitride thin films: kinetics and experiments. <i>CrystEngComm</i> , 2019 , 21, 3974-3981	3.3	13
161	Deposition and characterization of (Ti, Al)N coatings deposited by thermal LPCVD in an industrial reactor. <i>Surface and Coatings Technology</i> , 2019 , 358, 923-933	4.4	10
160	Reactive chemical vapor deposition of heteroepitaxial Ti _{1-x} Al _x N films. <i>CrystEngComm</i> , 2018 , 20, 1711-1715	3.5	5
159	Aluminum nitride thin films deposited by hydrogen plasma enhanced and thermal atomic layer deposition. <i>Surface and Coatings Technology</i> , 2018 , 347, 181-190	4.4	19
158	Chromium Carbide Growth by Direct Liquid Injection Chemical Vapor Deposition in Long and Narrow Tubes, Experiments, Modeling and Simulation. <i>Coatings</i> , 2018 , 8, 220	2.9	8
157	High-temperature oxidation resistance of chromium-based coatings deposited by DLI-MOCVD for enhanced protection of the inner surface of long tubes. <i>Surface and Coatings Technology</i> , 2018 , 349, 1048-1057	4.4	30
156	A niching genetic algorithm applied to optimize a SiC-bulk crystal growth system. <i>Journal of Crystal Growth</i> , 2017 , 468, 914-918	1.6	7
155	HVPE of aluminum nitride, film evaluation and multiscale modeling of the growth process. <i>Journal of Crystal Growth</i> , 2017 , 468, 235-240	1.6	2
154	Study of surface reaction during selective epitaxy growth of silicon by thermodynamic analysis and density functional theory calculation. <i>Journal of Crystal Growth</i> , 2017 , 468, 278-282	1.6	8
153	Chromium carbide growth at low temperature by a highly efficient DLI-MOCVD process in effluent recycling mode. <i>Surface and Coatings Technology</i> , 2017 , 332, 96-104	4.4	19
152	Evidence for a Cr metastable phase as a tracer in DLI-MOCVD chromium hard coatings usable in high temperature environment. <i>Applied Surface Science</i> , 2017 , 422, 198-206	6.7	11
151	Epitaxial Growth of AlN on (0001) Sapphire: Assessment of HVPE Process by a Design of Experiments Approach. <i>Coatings</i> , 2017 , 7, 136	2.9	10
150	Growth of boron nitride films on w-AlN (0001), 4° off-cut 4H-SiC (0001), W (110) and Cr (110) substrates by Chemical Vapor Deposition. <i>Crystal Research and Technology</i> , 2016 , 51, 231-238	1.3	5
149	Ni- and Cu-free Ti-based metallic glasses with potential biomedical application. <i>Intermetallics</i> , 2015 , 63, 86-96	3.5	18
148	Structure and deformation behavior of Zr ₂ Ni thin films deposited on Kapton substrates. <i>Surface and Coatings Technology</i> , 2014 , 239, 171-176	4.4	6
147	Influence of the V/III ratio in the gas phase on thin epitaxial AlN layers grown on (0001) sapphire by high temperature hydride vapor phase epitaxy. <i>Thin Solid Films</i> , 2014 , 573, 140-147	2.2	21

146	CFD modeling of the high-temperature HVPE growth of aluminum nitride layers on c-plane sapphire: from theoretical chemistry to process evaluation. <i>Theoretical Chemistry Accounts</i> , 2014 , 133, 1	1.9	11
145	Growth of Boron Nitride on (0001) AlN Templates by High Temperature-Hydride Vapor Phase Epitaxy (HT-HVPE). <i>Physics Procedia</i> , 2013 , 46, 102-106		8
144	Epitaxial growth of AlN on c-plane sapphire by High Temperature Hydride Vapor Phase Epitaxy: Influence of the gas phase N/Al ratio and low temperature protective layer. <i>Surface and Coatings Technology</i> , 2013 , 237, 118-125	4.4	13
143	High temperature chemical vapor deposition of aluminum nitride, growth and evaluation. <i>Surface and Coatings Technology</i> , 2013 , 230, 111-118	4.4	20
142	Effects of the V/III ratio on the quality of aluminum nitride grown on (0001) sapphire by high temperature hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 362-365		10
141	Crystallization during bending of a Pd-based metallic glass detected by x-ray microscopy. <i>Physical Review Letters</i> , 2012 , 109, 085501	7.4	23
140	Effects of AlN nucleation layers on the growth of AlN films using high temperature hydride vapor phase epitaxy. <i>Journal of Alloys and Compounds</i> , 2012 , 526, 103-109	5.7	40
139	Significance of initial stages on the epitaxial growth of AlN using high temperature halide chemical vapor deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 511-514		3
138	Growth and Characterization of Thick Polycrystalline AlN Layers by HTCVD. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H328	3.9	7
137	Investigation on AlN epitaxial growth and related etching phenomenon at high temperature using high temperature chemical vapor deposition process. <i>Journal of Crystal Growth</i> , 2011 , 335, 17-24	1.6	17
136	Aluminum nitride homoepitaxial growth on polar and non-polar AlN PVT substrates by high temperature CVD (HTCVD). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2019-2021		11
135	Developments of TaN ALD Process for 3D Conformal Coatings. <i>Chemical Vapor Deposition</i> , 2011 , 17, 284-295		5
134	Improvements of the Continuous Feed-Physical Vapor Transport Technique (CF-PVT) for the Seeded Growth of 3C-SiC Crystals. <i>Materials Science Forum</i> , 2010 , 645-648, 63-66	0.4	2
133	Study of the Spontaneous Nucleation of 3C-SiC Single Crystals Using CF-PVT Technique. <i>Materials Science Forum</i> , 2010 , 645-648, 55-58	0.4	3
132	Chemical vapour deposition and atomic layer deposition of amorphous and nanocrystalline metallic coatings: Towards deposition of multimetallic films. <i>Journal of Alloys and Compounds</i> , 2010 , 504, S422-S424	5.7	9
131	Coupled heat transfer and fluid dynamics modeling of high-temperature SiC solution growth. <i>Journal of Crystal Growth</i> , 2010 , 312, 155-163	1.6	49
130	Epitaxial and polycrystalline growth of AlN by high temperature CVD: Experimental results and simulation. <i>Surface and Coatings Technology</i> , 2010 , 205, 1294-1301	4.4	20
129	High temperature chemical vapor deposition of AlN/W ₁₈ Re coatings on bulk SiC. <i>Surface and Coatings Technology</i> , 2010 , 205, 1302-1306	4.4	3

128	Influence of the N/Al Ratio in the Gas Phase on the Growth of AlN by High Temperature Chemical Vapor Deposition (HTCVD). <i>Materials Science Forum</i> , 2009 , 615-617, 987-990	0.4	2
127	High-speed Growth and Characterization of Polycrystalline AlN Layers by High Temperature Chemical Vapor Deposition (HTCVD). <i>ECS Transactions</i> , 2009 , 25, 323-326	1	3
126	Top Seeded Solution Growth of 3C-SiC Single Crystals. <i>Materials Science Forum</i> , 2009 , 615-617, 41-44	0.4	6
125	Influence of total pressure and precursors flow rates on the growth of aluminium nitride by high temperature chemical vapor deposition (HTCVD). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S348-S351		3
124	Thermodynamic and experimental investigations on the growth of thick aluminum nitride layers by high temperature CVD. <i>Journal of Crystal Growth</i> , 2009 , 311, 3371-3379	1.6	23
123	Nucleation and Growth of 3C-SiC Single Crystals from the Vapor Phase. <i>Materials Science Forum</i> , 2009 , 615-617, 31-36	0.4	15
122	Growth of Thick AlN Layers by High Temperature CVD (HTCVD). <i>Materials Science Forum</i> , 2008 , 600-603, 1269-1272	0.4	4
121	Comparative Study of Differently Grown 3C-SiC Single Crystals with Birefringence Microscopy. <i>Materials Science Forum</i> , 2008 , 600-603, 71-74	0.4	2
120	Bulk Growth of SiC. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1069, 1		0
119	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. <i>Materials Science Forum</i> , 2008 , 600-603, 83-88.4		
118	Current and voltage distributions in a tubular solid oxide fuel cell (SOFC). <i>Journal of Applied Electrochemistry</i> , 2008 , 38, 497-505	2.6	13
117	Bulk growth of SiC [Review on advances of SiC vapor growth for improved doping and systematic study on dislocation evolution. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1239-1256	1.3	21
116	Prospects for 3C-SiC bulk crystal growth. <i>Journal of Crystal Growth</i> , 2008 , 310, 976-981	1.6	35
115	Chlorinated silicon carbide CVD revisited for polycrystalline bulk growth. <i>Surface and Coatings Technology</i> , 2007 , 201, 8888-8892	4.4	14
114	Chemical vapor deposition of thin films and coatings: Evaluation and process modeling. <i>Surface and Coatings Technology</i> , 2007 , 202, 790-797	4.4	11
113	Modeling of a SOFC fuelled by methane: From direct internal reforming to gradual internal reforming. <i>Chemical Engineering Science</i> , 2007 , 62, 1636-1649	4.4	115
112	Numerical modeling and experimental verification of modified-PVT crystal growth of SiC. <i>Journal of Crystal Growth</i> , 2007 , 303, 337-341	1.6	4
111	Numerical modeling of silicon carbide epitaxy in a horizontal hot-wall reactor. <i>Journal of Crystal Growth</i> , 2007 , 303, 334-336	1.6	3

110	Status of SiC bulk growth processes. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 6150-6158	3	21
109	Mechanism of Orientation Selection for the Growth Of (111) Twin Boundary Free 3C-SiC Single Crystals on Hexagonal Basis. <i>Materials Science Forum</i> , 2007 , 556-557, 199-202	0.4	
108	Modeling of a Solid Oxide Fuel Cell Fueled by Methane: Analysis of Carbon Deposition. <i>Journal of Fuel Cell Science and Technology</i> , 2007 , 4, 425-434		17
107	Numerical modeling of SiC-CVD in a horizontal hot-wall reactor. <i>Microelectronic Engineering</i> , 2006 , 83, 100-103	2.5	10
106	Growth and Doping Modeling of SiC-CVD in a Horizontal Hot-Wall Reactor. <i>Chemical Vapor Deposition</i> , 2006 , 12, 516-522		44
105	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 2		
104	Recent Progress of SiC Hot-Wall Epitaxy and Its Modeling. <i>Materials Science Forum</i> , 2006 , 527-529, 129-134		1
103	Characterization of Bulk 3C-SiC Single Crystals Grown on 4H-SiC by the CF-PVT Method. <i>Materials Science Forum</i> , 2006 , 527-529, 99-102	0.4	12
102	Processing of Poly-SiC Substrates with Large Grains for Wafer-Bonding. <i>Materials Science Forum</i> , 2006 , 527-529, 71-74	0.4	2
101	Modeling and Experimental Verification of SiC M-PVT Bulk Crystal Growth. <i>Materials Science Forum</i> , 2006 , 527-529, 75-78	0.4	2
100	Gas Fed Top-Seeded Solution Growth of Silicon Carbide. <i>Materials Science Forum</i> , 2006 , 527-529, 111-114	0.4	2
99	Giant Burgers Vector Micropipe-Dislocations in Silicon Carbide Investigated by Atomic Force Microscopy. <i>Materials Science Forum</i> , 2006 , 527-529, 435-438	0.4	0
98	In Situ Observation of Mass Transfer in the CF-PVT Growth Process by X-Ray Imaging. <i>Materials Science Forum</i> , 2006 , 527-529, 63-66	0.4	2
97	Growth of AlN and AlN-SiC Solid Solution by Sublimation Method. <i>Materials Science Forum</i> , 2006 , 527-529, 1501-1504	0.4	1
96	High-Temperature Nucleation of Cubic Silicon Carbide on (0001) Hexagonal-SiC Nominal Surfaces. <i>Crystal Growth and Design</i> , 2006 , 6, 2788-2794	3.5	26
95	Investigation of the charge carrier concentration in highly aluminum doped SiC using Raman scattering. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 558-561		5
94	Vapor growth of SiC bulk crystals and its challenge of doping. <i>Surface and Coatings Technology</i> , 2006 , 201, 4026-4031	4.4	10
93	High temperature processing of poly-SiC substrates from the vapor phase for wafer-bonding. <i>Surface and Coatings Technology</i> , 2006 , 201, 4014-4020	4.4	4

92	Large Area DPB Free (111) 6SiC Thick Layer Grown on (0001) 6SiC Nominal Surfaces by the CF-PVT Method. <i>Materials Science Forum</i> , 2005 , 483-485, 225-228	0.4	24
91	Control of the Supersaturation in the CFBVT Process for the Growth of Silicon Carbide Crystals: Research and Applications. <i>Crystal Growth and Design</i> , 2005 , 5, 1539-1544	3.5	38
90	Progress and Limits of the Numerical Simulation of SiC Bulk and Epitaxy Growth Processes. <i>Materials Science Forum</i> , 2005 , 483-485, 3-8	0.4	3
89	Study of 3C-SiC nucleation on (0 0 0 1) 6H-SiC nominal surfaces by the CF-PVT method. <i>Journal of Crystal Growth</i> , 2005 , 275, e609-e613	1.6	12
88	SiC single crystal growth by a modified physical vapor transport technique. <i>Journal of Crystal Growth</i> , 2005 , 275, e555-e560	1.6	34
87	Modeling of SiC-CVD on Si-face/C-face in a horizontal hot-wall reactor. <i>Journal of Crystal Growth</i> , 2005 , 275, e515-e520	1.6	12
86	Deposition of MgO thin film by liquid pulsed injection MOCVD. <i>Surface and Coatings Technology</i> , 2005 , 200, 1424-1429	4.4	24
85	Study of plasma mechanisms of hybrid a-SiOC:H low-k film deposition from decamethylcyclopentasiloxane and cyclohexene oxide. <i>Microelectronic Engineering</i> , 2005 , 82, 416-421	2.5	17
84	Optical mapping of aluminum doped p-type SiC wafers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 598-601	1.6	7
83	Numerical Analysis of Growth Condition on SiC-CVD in the Horizontal Hot-Wall Reactor. <i>Materials Science Forum</i> , 2005 , 483-485, 53-56	0.4	7
82	Micro-Optical Characterization Study of Highly p-Type Doped SiC:Al Wafers. <i>Materials Science Forum</i> , 2005 , 483-485, 393-396	0.4	3
81	Modified Physical Vapor Transport Growth of SiC - Control of Gas Phase Composition for Improved Process Conditions. <i>Materials Science Forum</i> , 2005 , 483-485, 25-30	0.4	8
80	Contribution of numerical simulation to silicon carbide bulk growth and epitaxy. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S1579-S1595	1.8	5
79	Nitrogen Doping of Epitaxial SiC: Experimental Evidence of the Re-Incorporation of Etched Nitrogen during Growth. <i>Materials Science Forum</i> , 2004 , 457-460, 731-734	0.4	1
78	Characterization of Thick 2-Inch 4H-SiC Layers Grown by the Continuous Feed-Physical Vapor Transport Method. <i>Materials Science Forum</i> , 2004 , 457-460, 91-94	0.4	6
77	In Situ SiC Feeding by Chemical Vapor Deposition for Bulk Growth. <i>Materials Science Forum</i> , 2004 , 457-460, 139-142	0.4	
76	Comparison between Various Chemical Systems for the CVD Step in the CF-PVT Crystal Growth Method. <i>Materials Science Forum</i> , 2004 , 457-460, 135-138	0.4	2
75	Electron Back Scattering Diffraction (EBSD) as a Tool for the Investigation of 3C-SiC Nucleation and Growth on 6H or 4H. <i>Materials Science Forum</i> , 2004 , 457-460, 387-390	0.4	10

74	Simulation of SiC deposition from SiH ₄ /C ₃ H ₈ /Ar/H ₂ mixtures in a cold-wall CVD reactor. <i>Surface and Coatings Technology</i> , 2004 , 177-178, 382-388	4.4	16
73	MOCVD processed platinum-aluminum coatings on titanium alloys. <i>Surface and Coatings Technology</i> , 2004 , 188-189, 49-54	4.4	6
72	Modeling and simulation of SiC CVD in the horizontal hot-wall reactor concept. <i>Journal of Crystal Growth</i> , 2004 , 267, 436-451	1.6	46
71	Free Growth of 4H-SiC by Sublimation Method. <i>Materials Science Forum</i> , 2004 , 457-460, 71-74	0.4	4
70	CVD on Bacteria Networks. <i>Chemical Vapor Deposition</i> , 2003 , 9, 179-180		
69	Vapor phase techniques for the fabrication of homoepitaxial layers of silicon carbide: process modeling and characterization. <i>Applied Surface Science</i> , 2003 , 212-213, 177-183	6.7	3
68	Continuous Feed Physical Vapor Transport. <i>Journal of the Electrochemical Society</i> , 2003 , 150, G653	3.9	25
67	A Study of HTCVD Renewing of the SiC Polycrystalline Source during the PVT Process. <i>Materials Science Forum</i> , 2003 , 433-436, 87-90	0.4	1
66	Heat Transfer Modeling of a New Crystal Growth Process. <i>Materials Science Forum</i> , 2003 , 433-436, 103-106	0.4	1
65	Defect Reduction in SiC Crystals Grown by the Modified Lely Method. <i>Materials Science Forum</i> , 2003 , 433-436, 83-86	0.4	
64	Investigation of Defects in 4H-SiC by Synchrotron Topography, Raman Spectroscopy Imaging and Photoluminescence Spectroscopy Imaging. <i>Materials Science Forum</i> , 2003 , 433-436, 265-268	0.4	2
63	Towards a Continuous Feeding of the PVT Growth Process: an Experimental Investigation. <i>Materials Science Forum</i> , 2003 , 433-436, 25-28	0.4	2
62	Experiment and Modeling of the Large-Area Etching and Growth Rate of Epitaxial SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 141-144	0.4	2
61	Simulation of the Large-Area Growth of Homoepitaxial 4H-SiC by Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2002 , 389-393, 223-226	0.4	4
60	Defects in sublimation-grown SiC bulk crystals. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 13009-13018	0.4	5
59	Solid-Phase Epitaxial Growth of Bulk SiC Single Crystals. <i>Materials Science Forum</i> , 2002 , 389-393, 143-146	0.4	1
58	Epitaxial silicon carbide simulations vs. experiments: etching, growth rates and aluminum/nitrogen doping. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 742, 141		2
57	Progress in 4H-SiC Bulk Growth. <i>Materials Science Forum</i> , 2001 , 353-356, 21-24	0.4	2

56	SiC Single Crystal Growth by Sublimation: Experimental and Numerical Results. <i>Materials Science Forum</i> , 2001 , 353-356, 7-10	0.4	14
55	Coupled Thermodynamic - Mass Transfer Modeling of the SiC Boule Growth by the PVT Method. <i>Materials Science Forum</i> , 2001 , 353-356, 61-64	0.4	1
54	Ab Initio Study of Silicon Carbide: Bulk and Surface Structures. <i>Materials Science Forum</i> , 2001 , 353-356, 111-114	0.4	2
53	Simulation of the large-area growth of homoepitaxial 4H-SiC by chemical vapor deposition. <i>European Physical Journal Special Topics</i> , 2001 , 11, Pr3-1079-Pr3-1086		2
52	Heat and mass transfer simulation of SiC boule growth by sublimation. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 640, 1		3
51	Combined thermodynamic and mass transport modeling for material processing from the vapor phase. <i>Thin Solid Films</i> , 2000 , 365, 264-274	2.2	5
50	Application of equilibrium thermodynamics to the development of diffusion barriers for copper metallization (invited). <i>Microelectronic Engineering</i> , 2000 , 50, 357-368	2.5	34
49	Evaporation Behavior of SiC Powder for Single Crystal Growth-An Experimental Study on Thermodynamics and Kinetics. <i>Materials Science Forum</i> , 2000 , 338-342, 91-94	0.4	10
48	Numerical Simulation of SiC Boule Growth by Sublimation. <i>Materials Science Forum</i> , 2000 , 338-342, 25-30	0.4	4
47	Progress in SiC Bulk Growth. <i>Materials Science Forum</i> , 2000 , 338-342, 13-16	0.4	10
46	Modelling of SiC sublimation growth process : Influence of experimental parameters on crystal shape. <i>European Physical Journal Special Topics</i> , 1999 , 09, Pr8-213-Pr8-219		4
45	Contribution to the modeling of CVD silicon carbide growth. <i>European Physical Journal Special Topics</i> , 1999 , 09, Pr8-205-Pr8-212		8
44	Thermodynamic Calculations as the Basis for CVD Production of Silicide Coatings. <i>MRS Bulletin</i> , 1999 , 24, 27-31	3.2	91
43	State of the art in the modelling of SiC sublimation growth. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 18-28	3.1	43
42	Modelling of SiC sublimation growth process: analyses of macrodefects formation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 82-85	3.1	8
41	Experimental Investigation of 4H-SiC Bulk Crystal Growth. <i>Materials Science Forum</i> , 1998 , 264-268, 17-20	0.4	5
40	Enlargement of SiC Crystals: Defect Formation at the Interfaces. <i>Materials Science Forum</i> , 1998 , 264-268, 45-48	0.4	8
39	Defects formation in sublimation grown 6H-SiC single crystal boules. <i>Diamond and Related Materials</i> , 1997 , 6, 1249-1261	3.5	14

38	Different macroscopic approaches to the modelling of the sublimation growth of SiC single crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 308-312	3.1	18
37	Macroscopic modelling of silicon carbide sublimation: toward a microscopic modelling of defect formation. <i>Surface and Coatings Technology</i> , 1997 , 94-95, 279-284	4.4	5
36	Thermodynamic Heat Transfer and Mass Transport Modeling of the Sublimation Growth of Silicon Carbide Crystals. <i>Journal of the Electrochemical Society</i> , 1996 , 143, 3727-3735	3.9	63
35	Thermodynamic equilibrium and mass transport coupled modelling of the chemical vapour deposition process. <i>Thin Solid Films</i> , 1996 , 281-282, 64-67	2.2	2
34	Improvement of the wear resistance of 316L stainless steel by laser surface alloying. <i>Surface and Coatings Technology</i> , 1996 , 80, 207-210	4.4	63
33	Hardening of 316L stainless steel by laser surface alloying. <i>Journal of Materials Science</i> , 1995 , 30, 3652-3657	4.5	28
32	The modelling routes for the chemical vapour deposition process: application to Si _{1-x} Gex deposition. <i>Applied Surface Science</i> , 1995 , 91, 34-43	6.7	2
31	Carbide-reinforced coatings on AISI 316 L stainless steel by laser surface alloying. <i>Surface and Coatings Technology</i> , 1995 , 76-77, 450-455	4.4	21
30	Croissance de couches de Si _{1-x} Gex par réaction chimique a partir d'une phase gazeuse : étude thermodynamique et analyse du transfert de matière. <i>Journal De Physique III</i> , 1995 , 5, 759-773		
29	Laser surface alloying of 316L stainless steel : different hardening routes and related microstructures. <i>European Physical Journal Special Topics</i> , 1994 , 04, C4-77-C4-80		2
28	Laser surface melting of mild steel with submicronic titanium carbide powders. <i>Journal of Materials Science</i> , 1994 , 29, 5121-5126	4.3	22
27	A coupled approach to thermochemical and mass transport modeling: application to TiSi ₂ deposition by CVD. <i>Applied Surface Science</i> , 1993 , 73, 71-81	6.7	7
26	Numerical modelling for CVD simulation and process optimization: coupled thermochemical and mass transport approaches. <i>Surface and Coatings Technology</i> , 1993 , 61, 274-281	4.4	9
25	The behaviour in SO ₂ at high temperatures of Fe ₂ B coatings on Fe obtained by ion beam, laser or pack-cementation techniques. <i>Corrosion Science</i> , 1993 , 35, 1073-1083	6.8	2
24	Laser surface alloying of Ti-6Al-4V with silicon for improved hardness and high-temperature oxidation resistance. <i>Materials Letters</i> , 1992 , 13, 204-211	3.3	13
23	Approche mécano-chimique de l'oxydation du zircaloy-4. <i>Surface and Coatings Technology</i> , 1991 , 46, 347-360	4.4	9
22	Laser surface alloying using metal salt precursors. <i>Surface and Coatings Technology</i> , 1991 , 45, 443-448	4.4	2
21	Traitements de surface par faisceaux de Haute energie. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 1989 , 120-121, 489-498	5.3	

20	Surface modification using lasers and ion beams. <i>Materials Science and Technology</i> , 1989 , 5, 806-812	1.5	7
19	MODELING OF COLD WALL CHEMICAL VAPOR DEPOSITION REACTORS (FOR SEMICONDUCTOR FABRICATION). <i>Journal De Physique Colloque</i> , 1989 , 50, C5-57-C5-65		2
18	Revêtements de carbure de bore sur fer laboré sous irradiation laser I. Elaboration des revêtements. <i>Surface and Coatings Technology</i> , 1988 , 35, 263-273	4.4	6
17	Revêtements de carbure de bore sur fer laboré sous irradiation laser II. Oxydation des revêtements. <i>Surface and Coatings Technology</i> , 1988 , 35, 275-283	4.4	1
16	Thermal Oxidation of Ion-Implanted Metals. <i>Defect and Diffusion Forum</i> , 1988 , 57-58, 189-206	0.7	6
15	Elaboration d'Alliages de surface sous irradiation laser. <i>Materials Science and Engineering</i> , 1987 , 88, 127-134		14
14	Laser-induced microstructural modifications in a vacuum plasma sprayed NiCoCrAlYTa coating. <i>Surface and Coatings Technology</i> , 1987 , 32, 85-95	4.4	14
13	High temperature oxidation of niobium superficially coated by laser treatment. <i>Materials Chemistry and Physics</i> , 1987 , 16, 423-432	4.4	9
12	A comparison between ion implantation and laser alloying of pure iron for oxidation resistance improvement. <i>Journal of Materials Science</i> , 1986 , 21, 2697-2704	4.3	13
11	Oxidation of ion-implanted niobium in the 300-700°C temperature range. <i>Materials Chemistry and Physics</i> , 1986 , 15, 45-60	4.4	6
10	A comparison between ion implantation and laser alloying of iron for oxidation resistance improvement. <i>Journal of Materials Science</i> , 1986 , 21, 4101-4106	4.3	3
9	Influence of laser surface boronizing on the high-temperature oxidation of nickel. <i>Materials Letters</i> , 1986 , 4, 102-106	3.3	3
8	Oxidation of ion-implanted metals. <i>Materials Science and Engineering</i> , 1985 , 69, 329-340		34
7	Oxidation of ion-implanted titanium in the 750-950 °C temperature range. <i>Journal of the Less Common Metals</i> , 1985 , 109, 45-56		12
6	La boruration superficielle du fer par faisceau laser. <i>Materiaux Et Techniques</i> , 1985 , 73, 699-708	0.6	7
5	Ion implantation into metals to prevent high temperature oxidation. <i>Nuclear Instruments & Methods in Physics Research</i> , 1983 , 209-210, 1011-1017		21
4	High temperature oxidation of bismuth-implanted iron. <i>Corrosion Science</i> , 1983 , 23, 1181-1187	6.8	5
3	La protection du nickel par siliciuration superficielle. <i>Materials Chemistry and Physics</i> , 1983 , 8, 153-161	4.4	3

2	The high temperature oxidation of aluminium-implanted iron. <i>Corrosion Science</i> , 1982 , 22, 239-249	6.8	15
1	Bulk Growth of SiC [Review on Advances of SiC Vapor Growth for Improved Doping and Systematic Study on Dislocation Evolution1-31		2